TEXAS INSTRUMENTS

LMK62E2-100M, LMK62E2-156M, LMK62E0-156M, LMK62A2-100M, LMK62A2-150M
LMK62A2-156M, LMK62A2-200M, LMK62A2-266M, LMK62I0-100M, LMK62I0-156M

ZHCSGL2D – DECEMBER 2016 – REVISED JULY 2018

LMK62XX 高性能低抖动振荡器

1 特性

- 低噪声，高性能
  - 抖动：Fout > 100MHz 时的典型值为 150fs (RMS)
  - 电源抑制比 (PSRR)：-60dBc，出色的电源抗扰度
- 支持的输出格式
  - 低压正发射极耦合逻辑 (LVPECL)、低压差分信令 (LVDS) 和高速收发器逻辑 (HCSL) 高达 400MHz
- 总频率容差为 ±50ppm (LMK62X2) 和 ±25ppm (LMK62X0)
- 3.3V 工作电压
- 工业温度范围（-40ºC 至 +85ºC）
- 5mm × 3.2mm 6 引脚封装，与行业标准 5032 XO 封装引脚兼容

2 应用

- 晶体振荡器、表面声波 (SAW) 振荡器或芯片振荡器的高性能替换产品
- 开关、路由器、网卡、基带装置 (BBU)、服务器、存储/SAN
- 测试和测量
- 医疗成像
- FPGA，处理器连接

3 说明

LMK62XX 器件是一款低抖动振荡器，可生成常用参考时钟。该器件在工厂预编程，可支持任何参考时钟频率；支持的输出格式是 LVPECL、LVDS 和 HCSL（最高 400MHz）。内部电源调节功能提供出色的电源纹波抑制 (PSRR)，降低了供电网络的成本和复杂性。该器件由单个 3.3V ± 5% 电源供电。

器件信息(1)

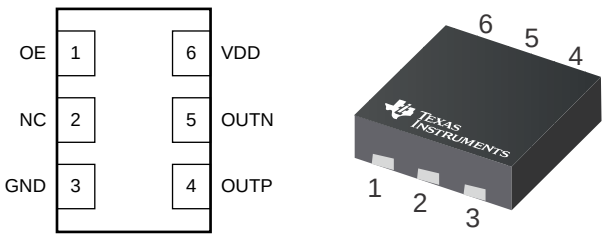
器件型号	封装	封装尺寸（标称值）
LMK62E2-100M	QFM (6)	5.00mm × 3.20mm
LMK62E2-156M	QFM (6)	5.00mm × 3.20mm
LMK62E0-156M	QFM (6)	5.00mm × 3.20mm
LMK62A2-100M	QFM (6)	5.00mm × 3.20mm
LMK62A2-150M	QFM (6)	5.00mm × 3.20mm
LMK62A2-156M	QFM (6)	5.00mm × 3.20mm
LMK62A2-200M	QFM (6)	5.00mm × 3.20mm
LMK62A2-266M	QFM (6)	5.00mm × 3.20mm
LMK62I0-100M	QFM (6)	5.00mm × 3.20mm
LMK62I0-156M	QFM (6)	5.00mm × 3.20mm

(1) 如需了解所有可用封装，请参阅产品说明书末尾的可订购产品附录。

输出频率选项

器件型号	输出频率 (MHz) 及格式	总频率稳定性 (ppm)
LMK62E2-100M	100 LVPECL	±50
LMK62E2-156M	156.25 LVPECL	±50
LMK62E0-156M	156.25 LVPECL	±25
LMK62A2-100M	100 LVDS	±50
LMK62A2-150M	150 LVDS	±50
LMK62A2-156M	156.25 LVDS	±50
LMK62A2-200M	200 LVDS	±50
LMK62A2-266M	266.66 LVDS	±50
LMK62I0-100M	100 HCSL	±25
LMK62I0-156M	156.25 HCSL	±25

引脚分配



目录

4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision C (December 2017) to Revision D **Page**

- Added V_{OS} minimum and maximum values to the *LVDS Output Characteristics* table ... 5

Changes from Revision B (June 2017) to Revision C **Page**

- 在器件列表中增加了 LMK62E2-100M、LMK62I0-100M 和 LMK62I0-156M ... 1

Changes from Revision A (April 2017) to Revision B **Page**

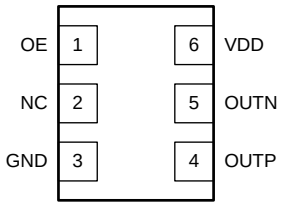
- 在器件列表中增加了 LMK62E0-156M、LMK62A2-100M、LMK62A2-150M、LMK62A2-156M、LMK62A2-200M 和 LMK62A2-266M ... 1

Changes from Original (December 2016) to Revision A **Page**

- 已更新生产数据的高级信息产品说明书 ... 1

5 Pin Configuration and Functions

SIA Package
6-pin QFM
Top View



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
POWER			
GND	3	Ground	Device ground
VDD	6	Analog	3.3-V power supply
OUTPUT BLOCK			
OUTP, OUTN	4, 5	Universal	Differential output pair (LVPECL, LVDS or HCSL).
DIGITAL CONTROL / INTERFACES			
NC	2	N/A	No connect
OE	1	LVCMOS	Output enable (internal pullup). When set to low, output pair is disabled and set at high impedance.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
VDD	Device supply voltage	–0.3	3.6	V
V_{IN}	Output voltage for logic inputs	–0.3	VDD + 0.3	V
V_{OUT}	Output voltage for clock outputs	–0.3	VDD + 0.3	V
T_J	Junction temperature		150	°C
T_{stg}	Storage temperature	–40	125	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
VDD	Device supply voltage	3.135	3.3	3.465	V
T_A	Ambient temperature	–40	25	85	°C
T_J	Junction temperature			105	°C
t_{RAMP}	VDD power-up ramp time	0.1		100	ms

6.4 Thermal Information

THERMAL METRIC(1)		LMK62XX (2) (3) (4) SIA (QFM) 6 PINS Airflow (LFM) 0	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	94.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	65.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	59	°C/W
ψ_{JT}	Junction-to-top characterization parameter	23.3	°C/W
ψ_{JB}	Junction-to-board characterization parameter	64.1	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.
(2) The package thermal resistance is calculated on a 4-layer JEDEC board.
(3) Connected to GND with 2 thermal vias (0.3-mm diameter).
(4) ψ_{JB} (junction to board) is used when the main heat flow is from the junction to the GND pad. Please refer to Thermal Considerations section for more information on ensuring good system reliability and quality.

6.5 Electrical Characteristics - Power Supply

VDD = 3.3 V ± 5%, T_A = –40°C to 85°C(1)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
IDD	Device current consumption	LVPECL(2)		95	110	mA
		LVDS		85	100	
		HCSL(3)		90	105	
IDD-PD	Device current consumption when output is disabled	OE = GND		70		mA

(1) See *Parameter Measurement Information* for relevant test conditions.
(2) On-chip power dissipation should exclude 40 mW, dissipated in the 150-Ω termination resistors, from total power dissipation.
(3) Excludes load current.

6.6 LVPECL Output Characteristics

VDD = 3.3 V ± 5%, T_A = –40°C to 85°C(1)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
f_{OUT}	Output frequency(2)				400	MHz
V_{OD}	Output voltage swing (V_{OH} – V_{OL})(2)		700	950	1200	mV
$V_{OUT, DIFF, PP}$	Differential output peak-to-peak swing			2 × $\lvert V_{OD} \rvert$		V
V_{OS}	Output common-mode voltage			VDD – 1.45		V
t_R / t_F	Output rise/fall time (20% to 80%)(3)			260	350	ps
ODC	Output duty cycle(3)		45%		55%	

(1) See *Parameter Measurement Information* for relevant test conditions.
(2) An output frequency over f_{OUT} max spec is possible, but output swing may be less than V_{OD} min spec.
(3) Ensured by characterization.

6.7 LVDS Output Characteristics

VDD = 3.3 V ± 5%, T_A = –40°C to 85°C(1)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
f_{OUT}	Output frequency(1)				400	MHz
V_{OD}	Output voltage swing (V_{OH} - V_{OL})(1)		300	390	480	mV
$V_{OUT, DIFF, PP}$	Differential output peak-to-peak swing			2 x $\|V_{OD}\|$		V
V_{OS}	Output common-mode voltage		1.125	1.2	1.375	V
t_R / t_F	Output rise/fall time (20% to 80%)(2)			260	350	ps
ODC	Output duty cycle(2)		45%		55%	
R_{OUT}	Differential output impedance			107		Ω

(1) An output frequency over f_{OUT} max spec is possible, but output swing may be less than V_{OD} min spec.
(2) Ensured by characterization.

6.8 HCSL Output Characteristics

VDD = 3.3 V ± 5%, T_A = –40°C to 85°C(1)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
f_{OUT}	Output frequency				400	MHz
V_{OH}	Output high voltage		660		900	mV
V_{OL}	Output low voltage		–100		100	mV
V_{CROSS}	Absolute crossing voltage(2)(3)		250		475	mV
$V_{CROSS-DELTA}$	Variation of V_{CROSS}(2)(3)		0		140	mV
dV/dt	Slew rate(4)		1		3	V/ns
ODC	Output duty cycle(4)		45%		55%	

(1) See *Parameter Measurement Information* for relevant test conditions.
(2) Measured from -150 mV to +150 mV on the differential waveform with the 300 mVpp measurement window centered on the differential zero crossing.
(3) Ensured by design.
(4) Ensured by characterization.

6.9 OE Input Characteristics

VDD = 3.3 V ± 5%, T_A = –40°C to 85°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{IH}	Input high voltage		1.4			V
V_{IL}	Input low voltage				0.6	V
I_{IH}	Input high current	V_{IH} = VDD	–40		40	µA
I_{IL}	Input low current	V_{IL} = GND	–40		40	µA
C_{IN}	Input capacitance			2		pF

6.10 Frequency Tolerance Characteristics

VDD = 3.3 V ± 5%, T_A = –40°C to 85°C(1)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
f_T	Total frequency tolerance	LMK62X2: All output formats, frequency bands and device junction temperature up to 105°C; includes initial freq tolerance, temperature & supply voltage variation, solder reflow and 5-year aging at 40°C	–50		50	ppm
		LMK62X0: All output formats, frequency bands and device junction temperature up to 105°C; includes initial freq tolerance, temperature & supply voltage variation, solder reflow and 5-year aging at 40°C	–25		25	ppm

(1) Ensured by characterization.

6.11 Power-On/Reset Characteristics (VDD)

VDD = 3.3 V ± 5%, T_A = –40°C to 85°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{THRESH}	Threshold voltage(1)		2.85		3	V
V_{DROOP}	Allowable voltage droop(2)				0.1	V
$t_{STARTUP}$	Start-up time (1)	Time elapsed from VDD at 3.135 V to output enabled			10	ms
t_{OE-EN}	Output enable time(2)	Time elapsed from OE at V_{IH} to output enabled			50	µs
t_{OE-DIS}	Output disable time(2)	Time elapsed from OE at V_{IL} to output disabled			50	µs

(1) Ensured by characterization.
(2) Ensured by design.

6.12 PSRR Characteristics

VDD = 3.3 V, T_A = 25°C(1)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
PSRR	Spurs induced by 50-mV power supply ripple(2)(3) at 156.25-MHz output, all output types	Sine wave at 50 kHz		–60		dBc
		Sine wave at 100 kHz		–60		
		Sine wave at 500 kHz		–60		
		Sine wave at 1 MHz		–60		

(1) See *Parameter Measurement Information* for relevant test conditions.
(2) Measured max spur level with 50 mVpp sinusoidal signal between 50 kHz and 1 MHz applied on VDD pin
(3) DJ_{SPUR} (ps, pk-pk) = [2*10(SPUR/20) / (π*f_{OUT})]*1e6, where PSRR or SPUR in dBc and f_{OUT} in MHz.

6.13 PLL Clock Output Jitter Characteristics

VDD = 3.3 V ± 5%, T_A = –40°C to 85°C(1)(2)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
RJ	RMS phase jitter(3) (12 kHz – 20 MHz)	f_{OUT} ≥ 100 MHz, all output types		150	250	fs RMS

(1) See *Parameter Measurement Information* for relevant test conditions.
(2) Phase jitter measured with Agilent E5052 signal source analyzer using a differential-to-single ended converter (balun or buffer).
(3) Ensured by characterization.

6.14 Additional Reliability and Qualification

PARAMETER	CONDITION / TEST METHOD
Mechanical Shock	MIL-STD-202, Method 213
Mechanical Vibration	MIL-STD-202, Method 204
Moisture Sensitivity Level	J-STD-020, MSL3

7 Parameter Measurement Information

7.1 Device Output Configurations

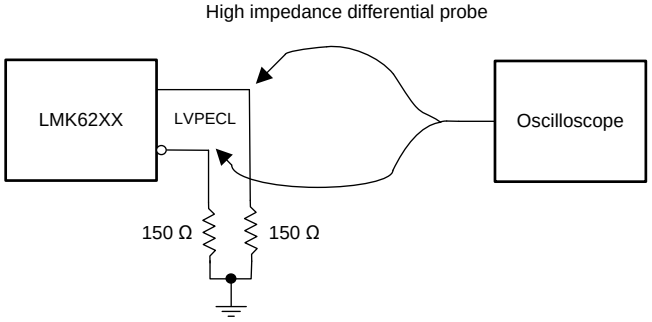


Figure 1. LVPECL Output DC Configuration During Device Test

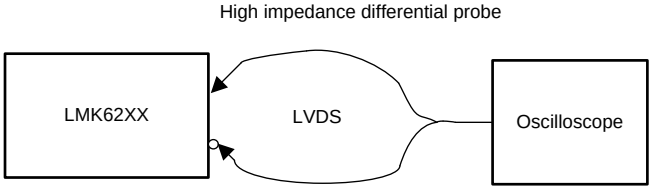


Figure 2. LVDS Output DC Configuration During Device Test

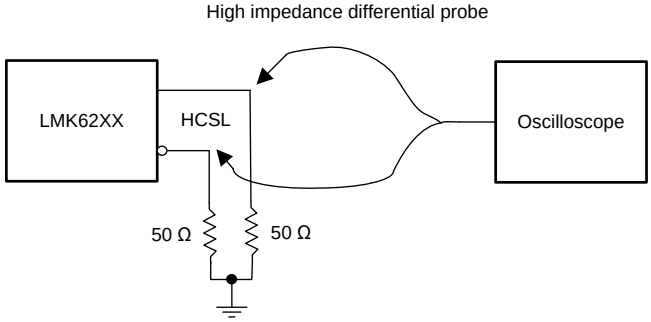


Figure 3. HCSL Output DC Configuration During Device Test (1)

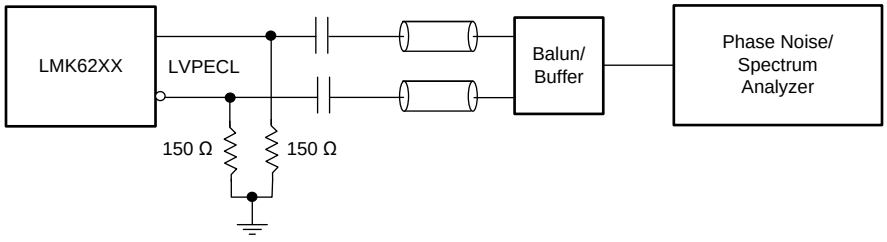


Figure 4. LVPECL Output AC Configuration During Device Test

(1) Also compatible with 85 Ω termination

Device Output Configurations (continued)

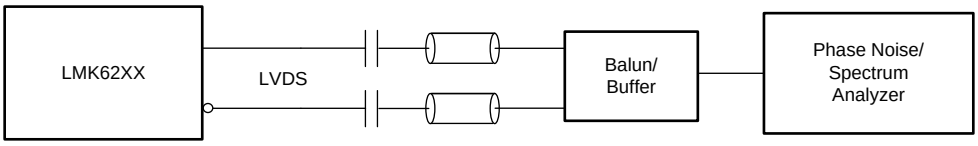


Figure 5. LVDS Output AC Configuration During Device Test

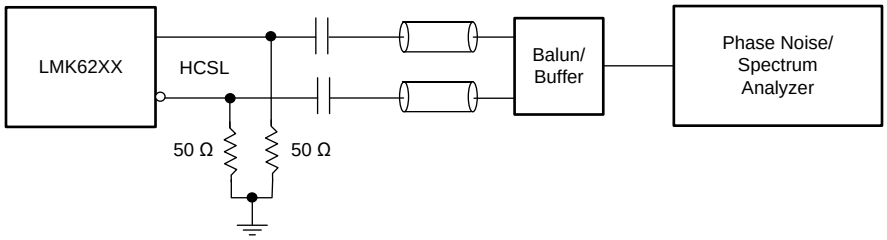


Figure 6. HCSL Output AC Configuration During Device Test

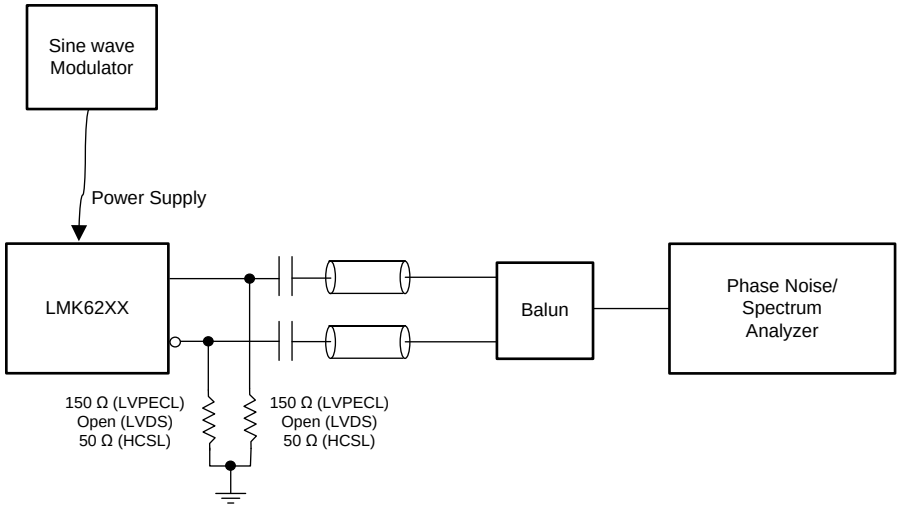


Figure 7. PSRR Test Setup

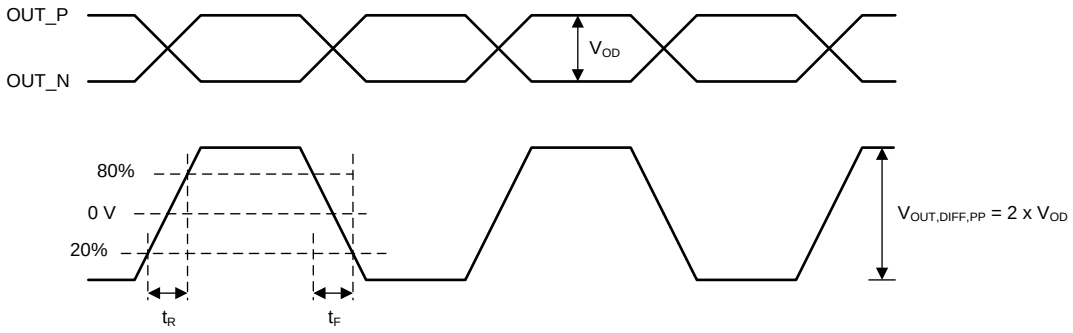


Figure 8. Differential Output Voltage and Rise/Fall Time

8 Power Supply Recommendations

For best electrical performance of LMK62XX, TI recommends using a combination of 10 µF, 1 µF, and 0.1 µF on the power-supply bypass network of the device. TI also recommends using component side mounting of the power-supply bypass capacitors and it is best to use 0201 or 0402 body size capacitors to facilitate signal routing. Keep the connections between the bypass capacitors and the power supply on the device as short as possible. Ground the other side of the capacitor using a low impedance connection to the ground plane. Figure 9 shows the layout recommendation for power supply decoupling of LMK62XX.

9 Layout

9.1 Layout Guidelines

The following sections provides recommendations for board layout, solder reflow profile and power supply bypassing when using LMK62XX to ensure good thermal / electrical performance and overall signal integrity of entire system.

9.1.1 Ensuring Thermal Reliability

The LMK62XX is a high-performance device. Therefore, pay careful attention to the device configuration and printed-circuit board (PCB) layout with respect to power consumption. The ground pin must be connected to the ground plane of the PCB through three vias or more, as shown in Figure 9, to maximize thermal dissipation out of the package.

Equation 1 shows the relationship between the PCB temperature around the LMK62XX and the junction temperature.

$$T_B = T_J - \Psi_{JB} \times P \quad (1)$$

where

- T_B: PCB temperature around the LMK62XX
- T_J: Junction temperature of LMK62XX
- Ψ_{JB}: Junction-to-board thermal resistance parameter of LMK62XX (64.1°C/W without airflow)
- P: On-chip power dissipation of LMK62XX

To ensure that the maximum junction temperature of LMK62XX is below 105°C, it can be calculated that the maximum PCB temperature without airflow should be at 81°C or below when the device is optimized for best performance, resulting in maximum on-chip power dissipation of 0.36 W.

9.1.2 Best Practices for Signal Integrity

For best electrical performance and signal integrity of entire system with LMK62XX, TI recommends routing vias into decoupling capacitors and then into the LMK62XX. TI also recommends increasing the via count and width of the traces wherever possible. These steps ensure lowest impedance and shortest path for high frequency current flow. Figure 9 shows the layout recommendation for LMK62XX.

Layout Guidelines (continued)

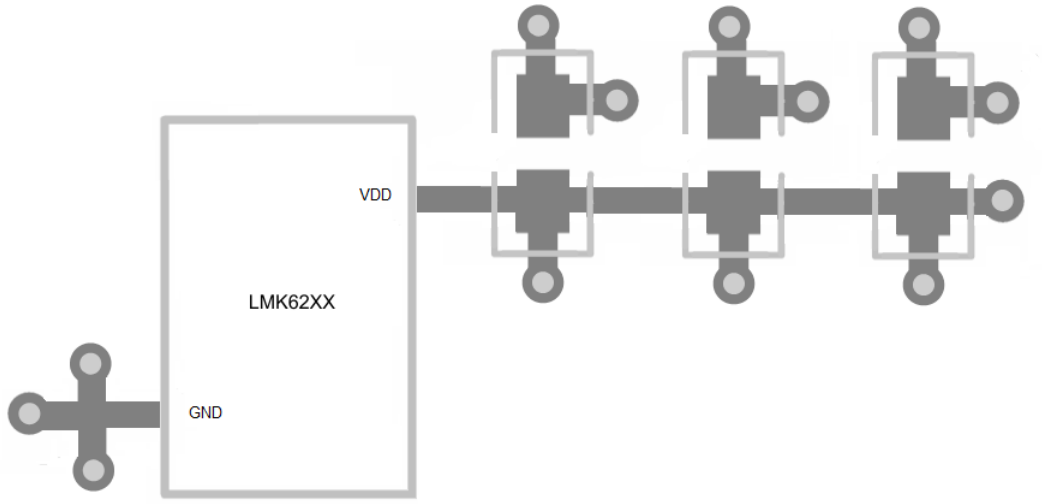


Figure 9. LMK62XX Layout Recommendation for Power Supply and Ground

9.1.3 Recommended Solder Reflow Profile

TI recommends following the recommendations set by the solder paste supplier to optimize flux activity and to achieve proper melting temperatures of the alloy within the guidelines of J-STD-20. Processing LMK62XX with the lowest peak temperature possible while also remaining below the components peak temperature rating as listed on the MSL label is preferred. The exact temperature profile would depend on several factors including maximum peak temperature for the component as rated on the MSL label, board thickness, PCB material type, PCB geometries, component locations, sizes, densities within PCB, as well as the recommended soldering profile from the manufacturer, and capability of the reflow equipment to as confirmed by the SMT assembly operation.

10 器件和文档支持

10.1 接收文档更新通知

要接收文档更新通知，请导航至 TI.com.cn 上的器件产品文件夹。单击右上角的*通知我* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

10.2 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 《使用条款》。

TI E2E™ 在线社区 ***TI 的工程师对工程师 (E2E) 社区。*** 此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 ***TI 参考设计支持*** 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

10.3 商标

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

10.4 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

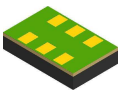
10.5 术语表

SLYZ022 — *TI 术语表*。

这份术语表列出并解释术语、缩写和定义。

11 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此产品说明书的浏览器版本，请查阅左侧的导航栏。

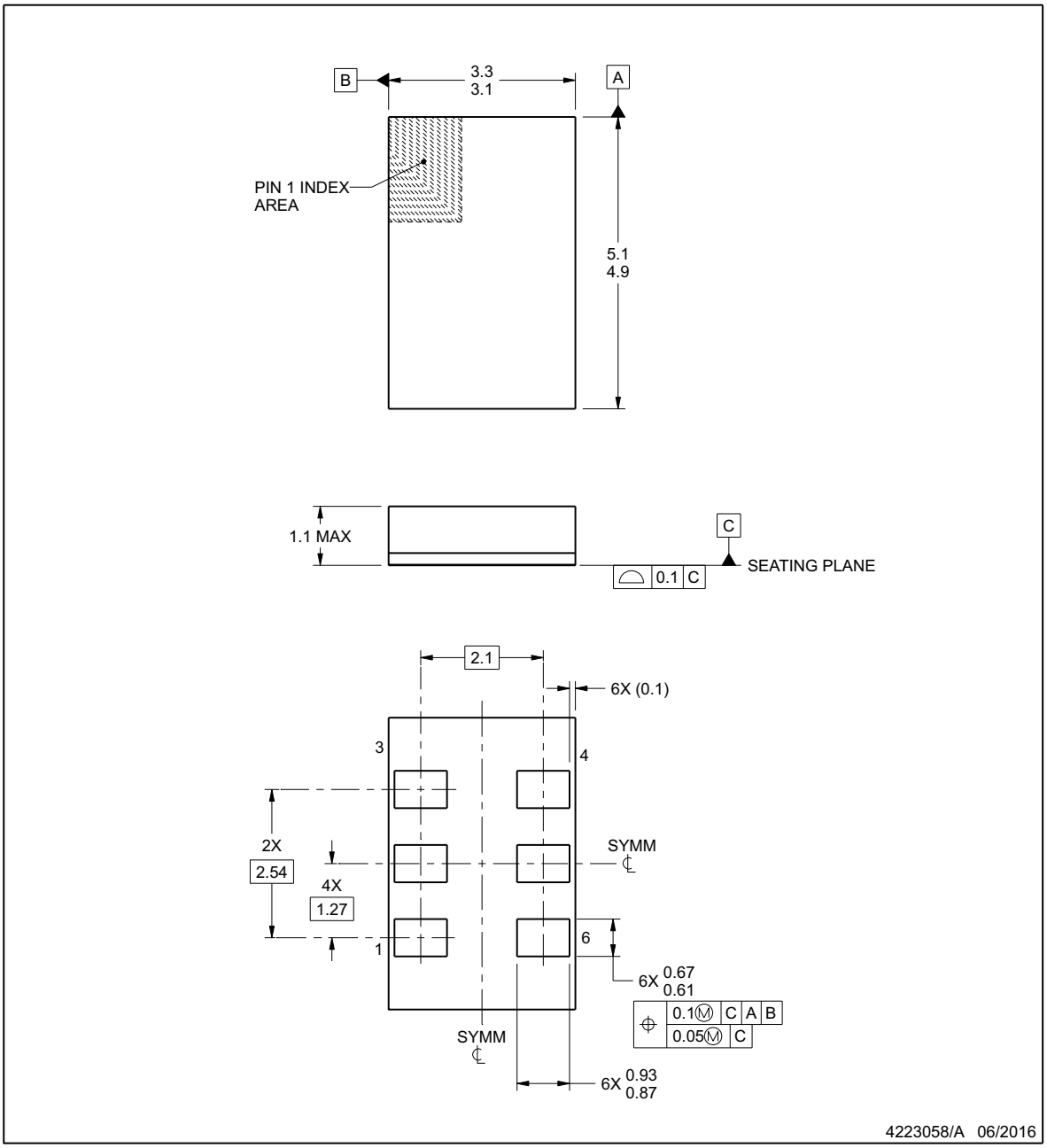


PACKAGE OUTLINE

SIA0006B

QFM - 1.1 mm max height

QUAD FLAT MODULE



NOTES:

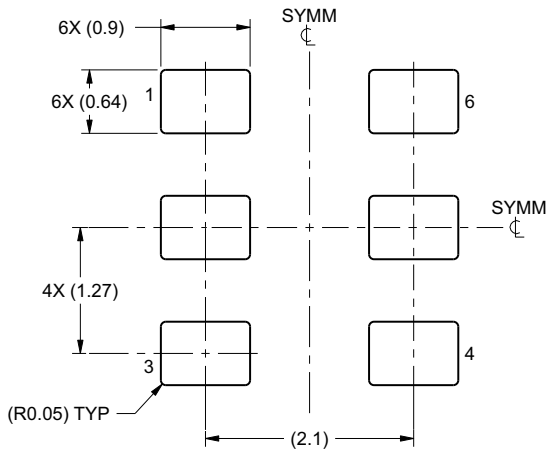
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

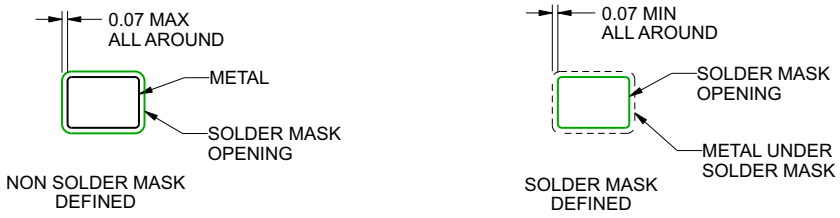
SIA0006B

QFM - 1.1 mm max height

QUAD FLAT MODULE



LAND PATTERN EXAMPLE
1:1 RATIO WITH PACKAGE SOLDER PADS
SCALE:15X



SOLDER MASK DETAILS
NOT TO SCALE

4223058/A 06/2016

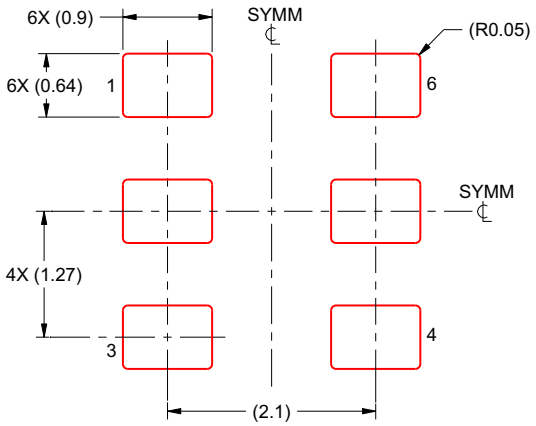
NOTES: (continued)

3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

EXAMPLE STENCIL DESIGN

SIA0006B **QFM - 1.1 mm max height**

QUAD FLAT MODULE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

PRINTED SOLDER COVERAGE BY AREA
ALL PADS: 100%
SCALE:15X

4223058/A 06/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMK62A2-100M00SIAR	ACTIVE	QFM	SIA	6	2500	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62A2 10000	Samples
LMK62A2-100M00SIAT	ACTIVE	QFM	SIA	6	250	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62A2 10000	Samples
LMK62A2-150M00SIAR	ACTIVE	QFM	SIA	6	2500	RoHS & Green	NIAU	Level-3-260C-168 HR	-40 to 85	62A2 15000	Samples
LMK62A2-150M00SIAT	ACTIVE	QFM	SIA	6	250	RoHS & Green	NIAU	Level-3-260C-168 HR	-40 to 85	62A2 15000	Samples
LMK62A2-156M25SIAR	ACTIVE	QFM	SIA	6	2500	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62A2 15625	Samples
LMK62A2-156M25SIAT	ACTIVE	QFM	SIA	6	250	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62A2 15625	Samples
LMK62A2-200M00SIAR	ACTIVE	QFM	SIA	6	2500	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62A2 20000	Samples
LMK62A2-200M00SIAT	ACTIVE	QFM	SIA	6	250	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62A2 20000	Samples
LMK62A2-266M66SIAR	ACTIVE	QFM	SIA	6	2500	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62A2 26666	Samples
LMK62A2-266M66SIAT	ACTIVE	QFM	SIA	6	250	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62A2 26666	Samples
LMK62E0-156M25SIAR	ACTIVE	QFM	SIA	6	2500	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62E0 15625	Samples
LMK62E0-156M25SIAT	ACTIVE	QFM	SIA	6	250	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62E0 15625	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMK62E2-100M00SIAR	ACTIVE	QFM	SIA	6	2500	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62E2 10000	Samples
LMK62E2-100M00SIAT	ACTIVE	QFM	SIA	6	250	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62E2 10000	Samples
LMK62E2-156M25SIAR	ACTIVE	QFM	SIA	6	2500	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62E2 15625	Samples
LMK62E2-156M25SIAT	ACTIVE	QFM	SIA	6	250	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62E2 15625	Samples
LMK62I0-100M00SIAR	ACTIVE	QFM	SIA	6	2500	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62I0 10000	Samples
LMK62I0-100M00SIAT	ACTIVE	QFM	SIA	6	250	RoHS (In Work) & Green (In Work)	NIAU	Level-3-260C-168 HR	-40 to 85	62I0 10000	Samples
LMK62I0-156M25SIAR	ACTIVE	QFM	SIA	6	2500	RoHS & Green	NIAU	Level-3-260C-168 HR	-40 to 85	62I0 15625	Samples
LMK62I0-156M25SIAT	ACTIVE	QFM	SIA	6	250	RoHS & Green	NIAU	Level-3-260C-168 HR	-40 to 85	62I0 15625	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

重要声明和免责声明

TI 均以“原样”提供技术性及可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证其中不含任何瑕疵，且不做任何明示或暗示的担保，包括但不限于对适销性、适合某特定用途或不侵犯任何第三方知识产权的暗示担保。

所述资源可供专业开发人员应用TI 产品进行设计使用。您将对以下行为独自承担全部责任：(1) 针对您的应用选择合适的TI 产品；(2) 设计、验证并测试您的应用；(3) 确保您的应用满足相应标准以及任何其他安全、安保或其他要求。所述资源如有变更，恕不另行通知。TI 对您使用所述资源的授权仅限于开发资源所涉及TI 产品的相关应用。除此之外不得复制或展示所述资源，也不提供其它TI或任何第三方的知识产权授权许可。如因使用所述资源而产生任何索赔、赔偿、成本、损失及债务等，TI对此概不负责，并且您须赔偿由此对TI 及其代表造成的损害。

TI 所提供产品均受TI 的销售条款 (http://www.ti.com.cn/zh-cn/legal/termsofsale.html) 以及ti.com.cn上或随附TI产品提供的其他可适用条款的约束。TI提供所述资源并不扩展或以其他方式更改TI 针对TI 产品所发布的可适用的担保范围或担保免责声明。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122